On the array of 1 at.% Ce-doped ZnO nanorod prepared by electrochemical deposition with their structure and characterization J.C. Lin, J.W. Hung, W.H. Shiu, H.Y. Chiang **4()**

Abstract

ZnO-based semiconductor is a transparent material for many applications, such as some electronic devices, light emitting diode, fluorescent material, sensor, and solar cell. In this study, ZnO-nanorods were doped with 1 at.% Ce on ITO substrate by electrodeposition. We prepared our electrolyte from ZnCl2 and H2O2, and 0.04M KCl. Our purpose is to improve ZnO's transmittance, and compare electrochemical curve with different precursor, CeCl3 and Ce(NO3)3. We also investigate the influence when using different concentration of H2O2. We did many analysis to proof our result, such as Field-emission scanning electron microscope(FE-SEM), Alpha step, X-ray diffraction(XRD), X-ray photoelectron spectrometer(XPS).

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Experimental







and 881.9 eV which indicates that

XPS images of (c)CeCl3 and (d)Ce(NO3)3 doped ZnO nanorods



the current will increase with the increasing concentration of H₂O₂.

[1] 黃茂嘉,「奈米氧化鋅結構之電化學研製及其在

發光二極體之應用」,中央大學,碩士論文,民國

[2]X.Y. Chen, F. Fang, A.M.C. Ng et al. *Thin Solid*

Reference

Films **520**, 1125–1130, (2011)

100年。

Conclusion

 \checkmark The transmittance exceed 90% which reach our goals. \checkmark The best potential in our study to do cathode deposition is -1.0 V. \checkmark Both Ce(NO₃)₃ and CeCl₃ are hexagonal wurtzite structure. ✓ There are good result of SEM when the concentration of H₂O₂ between 2.45 mM and 4 mM.